

### MBR120150CT thru MBR120200CTR

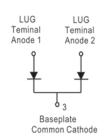
# Silicon Power Schottky Diode

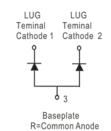
 $V_{RRM} = 150 V - 200 V$ 

 $I_{F(AV)} = 120 A$ 

#### **Features**

- High Surge Capability
- $\bullet$  Types from 150 V to 200 V  $V_{\text{RRM}}$
- Not ESD Sensitive







**Twin Tower Package** 





#### Maximum ratings, at T<sub>i</sub> = 25 °C, unless otherwise specified ("R" devices have leads reversed)

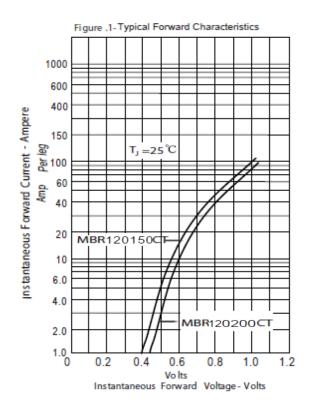
Parameter	Symbol	Conditions	MBR120150CT(R)	MBR120200CT(R)	Unit
Repetitive peak reverse voltage	$V_{RRM}$		150	200	V
RMS reverse voltage	V <sub>RMS</sub>		106	141	V
DC blocking voltage	$V_{DC}$		150	200	V
Operating temperature	T <sub>j</sub>		-55 to 150	-55 to 150	°C
Storage temperature	$T_{stg}$		-55 to 150	-55 to 150	°C

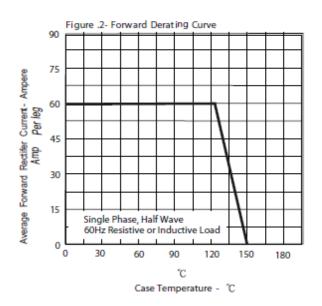
#### Electrical characteristics, at Tj = 25 °C, unless otherwise specified

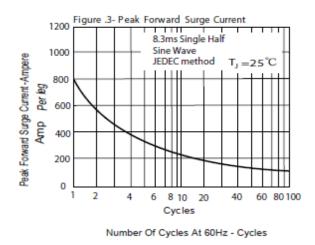
Symbol	Conditions	MBR120150CT(R)	MBR120200CT(R)	Unit	
I <sub>F(AV)</sub>	T <sub>C</sub> = 125 °C	120	120	А	
I <sub>FSM</sub>	$t_p = 8.3 \text{ ms}$ , half sine	800	800	А	
V <sub>F</sub>	I <sub>FM</sub> = 60 A, T <sub>j</sub> = 25 °C	0.88	0.92	V	
	T <sub>j</sub> = 25 °C	1	1		
$I_R$	$T_j = 100  ^{\circ}C$	10	10	mA	
	$T_j = 150  ^{\circ}C$	30	30		
S					
$R_{\Theta JC}$		0.80	0.80	°C/W	
	I <sub>F(AV)</sub> I <sub>FSM</sub> V <sub>F</sub> I <sub>R</sub>	$I_{F(AV)} \qquad \qquad T_{C} = 125  ^{\circ}\text{C}$ $I_{FSM} \qquad \qquad t_{p} = 8.3  \text{ms, half sine}$ $V_{F} \qquad \qquad I_{FM} = 60  \text{A, } T_{j} = 25  ^{\circ}\text{C}$ $T_{j} = 25  ^{\circ}\text{C}$ $T_{j} = 100  ^{\circ}\text{C}$ $T_{j} = 150  ^{\circ}\text{C}$	$I_{F(AV)} \qquad T_C = 125  ^{\circ}\text{C} \qquad \qquad 120$ $I_{FSM} \qquad t_p = 8.3  \text{ms, half sine} \qquad \qquad 800$ $V_F \qquad I_{FM} = 60  \text{A, } T_j = 25  ^{\circ}\text{C} \qquad \qquad 0.88$ $T_j = 25  ^{\circ}\text{C} \qquad \qquad 1$ $I_R \qquad T_j = 100  ^{\circ}\text{C} \qquad \qquad 10$ $T_j = 150  ^{\circ}\text{C} \qquad \qquad 30$	$I_{F(AV)} \qquad T_C = 125  ^{\circ}C \qquad 120 \qquad 120$ $I_{FSM} \qquad t_p = 8.3  \text{ms, half sine} \qquad 800 \qquad 800$ $V_F \qquad I_{FM} = 60  \text{A, } T_j = 25  ^{\circ}C \qquad 0.88 \qquad 0.92$ $T_j = 25  ^{\circ}C \qquad 1 \qquad 1$ $I_R \qquad T_j = 100  ^{\circ}C \qquad 10 \qquad 10$ $T_j = 150  ^{\circ}C \qquad 30 \qquad 30$	

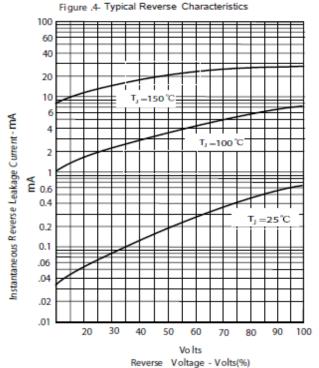


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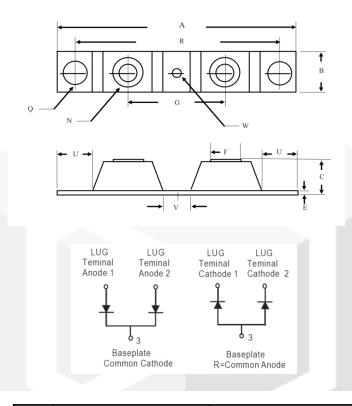




# MBR120150CT thru MBR120200CTR

#### Package dimensions and terminal configuration

Product is marked with part number and terminal configuration.



DIM	Inc	hes	Millimeters			
İ	Min	Max	Min	Max		
A	3.630			92.40		
В	0.700	0.800	17.78	20.32		
С		0.650		16.51		
Е	0.130	0.141	3.30	3.60		
F	0.482	0.490	12.25	12.45		
G	1.368	BSC	34.75	BSC		
N	1/4-20 UNC FULL					
Q	0.275	0.290	6.99	7.37		
R	3.150	BSC	80.01	BSC		
U	0.600		15.24			
V	0.312	0.370	7.92	9.40		
W	0.180 0.195		4.57 4.95			

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<u>25.330.4753.1</u> <u>25.</u>	330.5253.1	25.334.3253.1	25.334.3353.1	25.350.2053.0	25.352.4753.1	25.522.3253.0	<u>T483C</u> <u>T484C</u>	T485F T485H
T512F-YEB T513	<u>F T514F T</u>	<u>T612FSE</u>	25.161.3453.0	25.179.2253.0	25.194.3253.0	25.325.1253.1	25.326.4253.1	25.330.0953.1
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25.640.5053.0								